

# ATM2310NSA

## N-Channel Enhancement Mode Field Effect Transistor

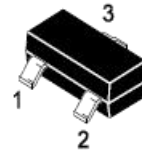
Drain-Source Voltage: 60V

Drain Current: 3A

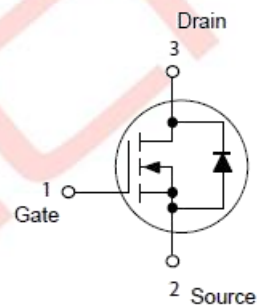
### Description

The ATM2310NSA uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as Battery protection or in other Switching application.

SOT-23



1 Gate 2 Source 3 Drain



### Features

- High power and current handling capability
- Surface mount package
- $R_{DS(ON)} < 100m\Omega$  ( $V_{GS} = 10V$ )
- $R_{DS(ON)} < 110m\Omega$  ( $V_{GS} = 4.5V$ )

### Application

- Battery Switch
- DC/DC Converter

### Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	3	A
Pulsed Drain Current <sup>1)</sup>	$I_{DM}$	10	
Maximum Power Dissipation	$P_D$	1	W
Thermal Resistance from Junction to Ambient <sup>2)</sup>	$R_{\theta JA}$	125	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55~ +150	

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## Electrical characteristics (T<sub>A</sub>=25 °C, unless otherwise noted)

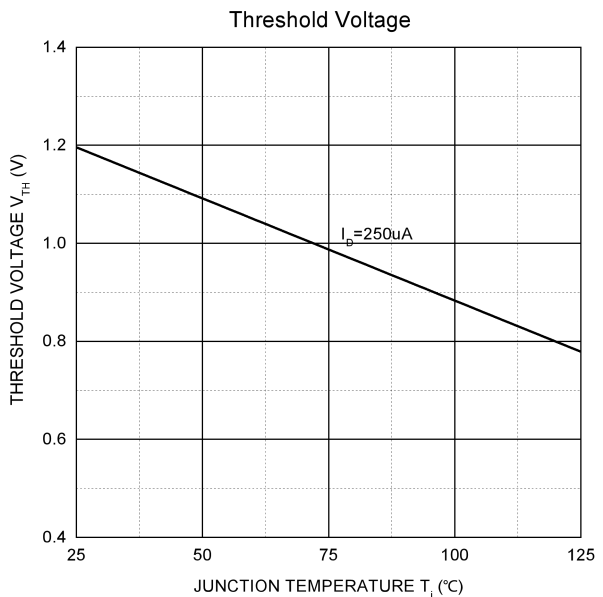
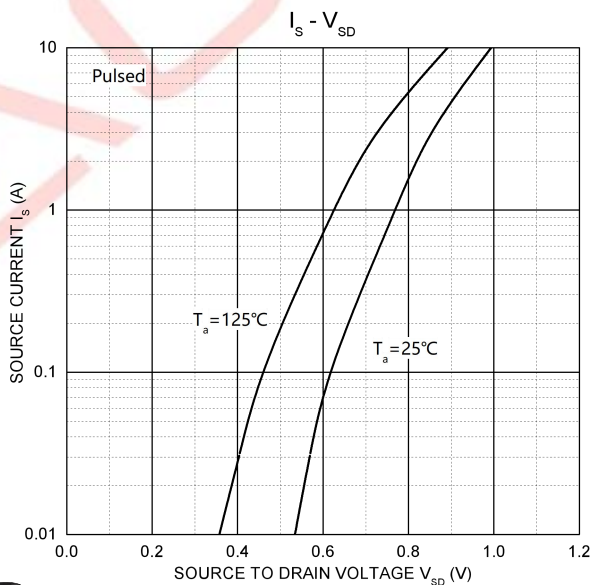
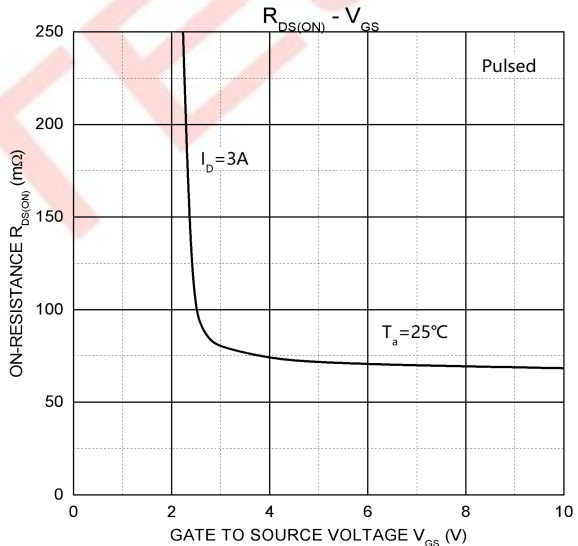
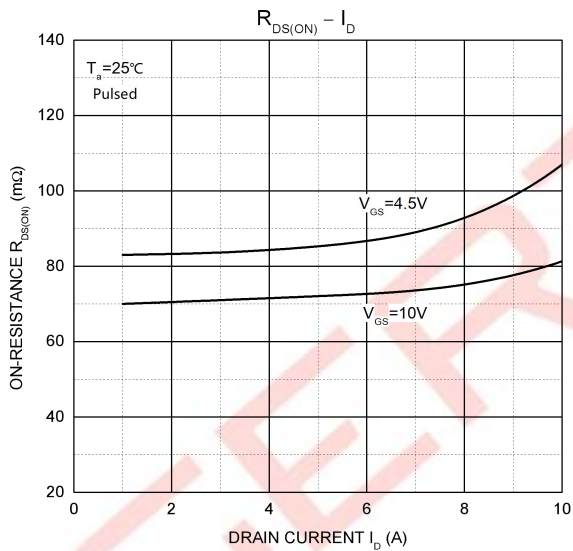
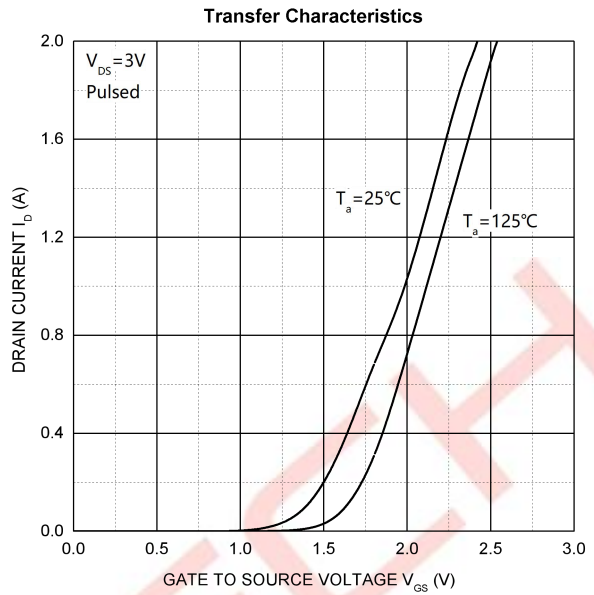
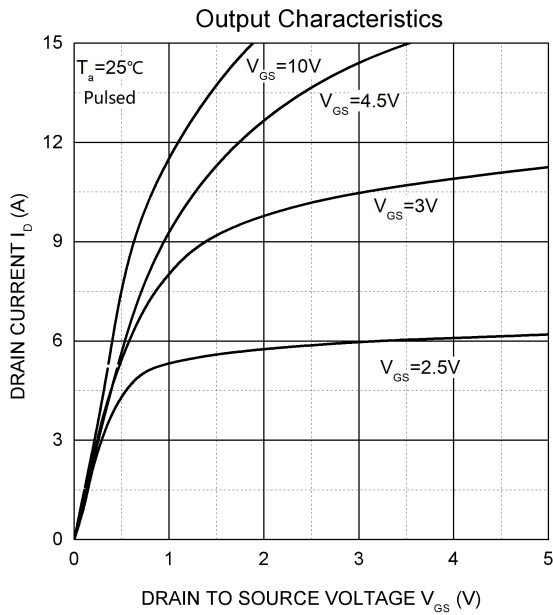
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =48V, V <sub>GS</sub> = 0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> = 0V			±100	nA
Gate Threshold Voltage <sup>3)</sup>	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1		2.5	V
Drain-Source On-Resistance <sup>3)</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =2A			100	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1A			110	
<b>Dynamic characteristics<sup>4)</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f =1MHz		250		pF
Output Capacitance	C <sub>oss</sub>			26		
Reverse Transfer Capacitance	C <sub>rss</sub>			20		
<b>Switching Characteristics<sup>4)</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A		7		nC
Gate-Source Charge	Q <sub>gs</sub>			1.2		
Gate-Drain Charge	Q <sub>gd</sub>			1.5		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =30V, I <sub>D</sub> =1.5A, R <sub>GEN</sub> =1Ω		6.5		ns
Turn-On Rise Time	t <sub>r</sub>			15.2		
Turn-Off Delay Time	t <sub>d(off)</sub>			15.2		
Turn-Off Fall Time	t <sub>f</sub>			10.3		
<b>Source-Drain Diode characteristics<sup>4)</sup></b>						
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V			1.2	V

### Notes:

- 1) Repetitive rating: Pulse width limited by junction temperature.
- 2) Surface mounted on FR4 board, t≤10s.
- 3) Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.
- 4) Guaranteed by design, not subject to production.

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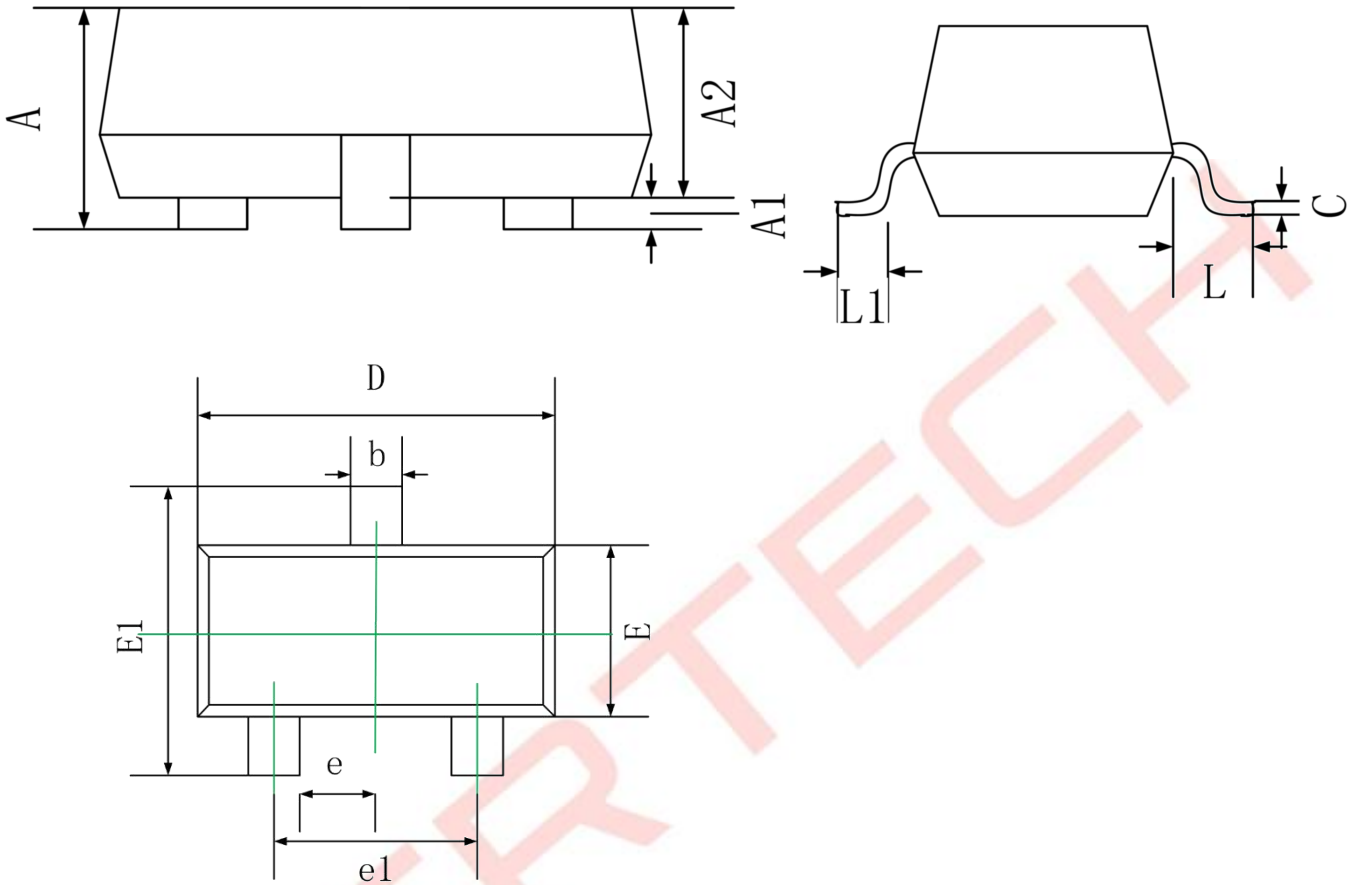
## Typical Characteristics Curves



# ATM2310NSA

## Package Outline

SOT-23

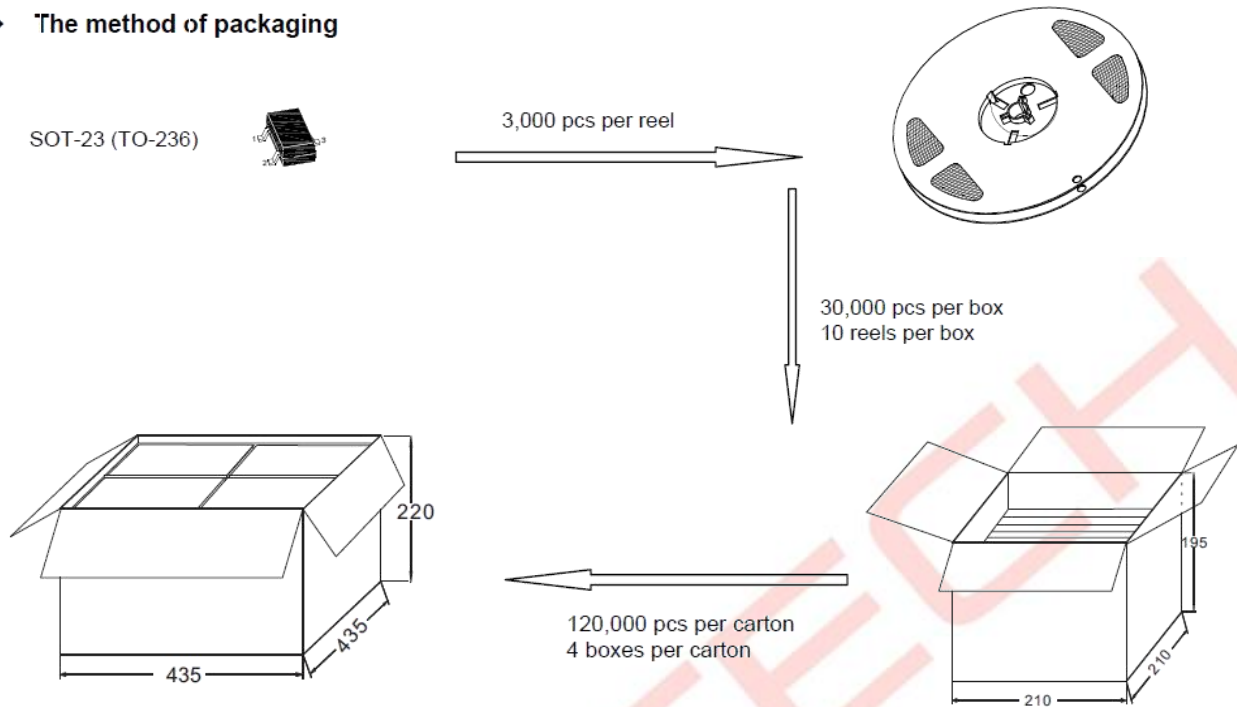


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50

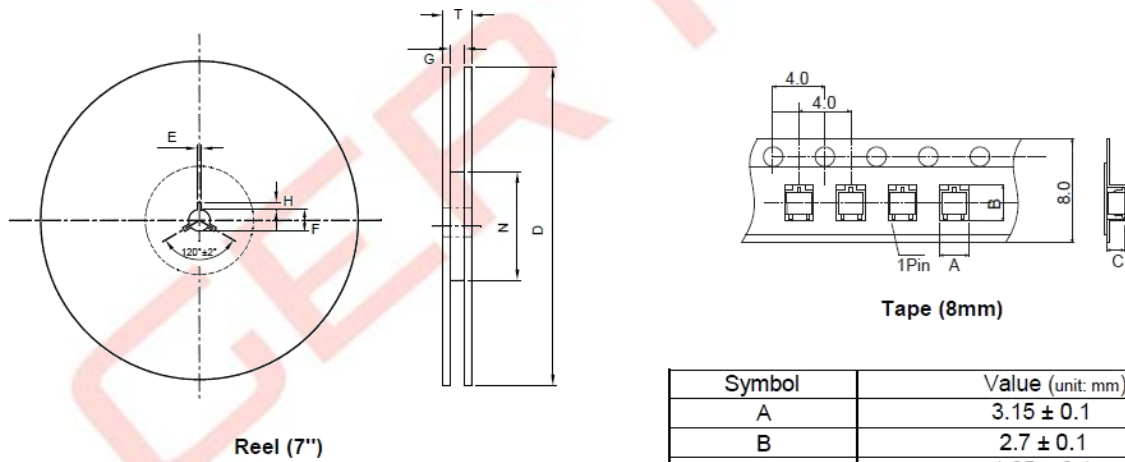
# ATM2310NSA

## Package Specifications

### ◆ The method of packaging



### ◆ Embossed tape and reel data



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